











SN74LVC2G241

SCES210P - APRIL 1999 - REVISED JANUARY 2019

SN74LVC2G241 Dual Buffer and Driver With 3-State Outputs

Features

- Available in the Texas Instruments NanoFree™ Package
- Supports 5-V V_{CC} Operation
- Inputs Accept Voltages to 5.5 V
- Max t_{pd} of 4.1 ns at 3.3 V
- Low Power Consumption, 10-µA Maximum I_{CC}
- ±24-mA Output Drive at 3.3 V
- Typical V_{OLP} (Output Ground Bounce) $< 0.8 \text{ V at V}_{CC} = 3.3 \text{ V}, T_A = 25^{\circ}\text{C}$
- Typical V_{OHV} (Output V_{OH} Undershoot) >2 V at V_{CC} = 3.3 V, T_A = 25°C
- I_{off} Supports Live Insertion, Partial-Power-Down Mode, and Back-Drive Protection
- Can Be Used as a Down Translator to Translate Inputs From a Max of 5.5 V Down to the V_{CC} Level
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Protection Exceeds JESD 22
 - 2000-V Human-Body Model (A114-A)
 - 200-V Machine Model (A115-A)
 - 1000-V Charged-Device Model (C101)

Applications

- **AV Receivers**
- Blu-ray Players and Home Theaters
- **DVD Recorders and Players**
- Desktop or Notebook PCs
- Digital Radio or Internet Radio Players
- Digital Video Cameras (DVC)
- **Embedded PCs**
- **GPS: Personal Navigation Devices**
- Mobile Internet Devices
- **Network Projector Front-Ends**
- Portable Media Players
- Pro Audio Mixers

3 Description

This dual buffer and line driver is designed for 1.65-V to 5.5-V V_{CC} operation.

The SN74LVC2G241 device is designed specifically to improve both the performance and density of 3state memory-address drivers, clock drivers, and busoriented receivers and transmitters.

NanoFree package technology is breakthrough in IC packaging concepts, using the die as the package.

The SN74LVC2G241 device is organized as two 1-bit line drivers with separate output-enable (10E, 20E) inputs. When $1\overline{OE}$ is low and 2OE is high, the device passes data from the A inputs to the Y outputs. When 10E is high and 20E is low, the outputs are in the high-impedance state.

To ensure the high-impedance state during power up or power down, OE should be tied to V_{CC} through a pullup resistor, and OE should be tied to GND through a pulldown resistor; the minimum value of the resistor is determined by the current-sinking or the current-sourcing capability of the driver.

This device is fully specified for partial-power-down applications using Ioff. The Ioff circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

Device Information⁽¹⁾

PART NUMBER	PACKAGE	BODY SIZE (NOM)
SN74LVC2G241DCT	SM8 (8)	2.95 mm × 2.80 mm
SN74LVC2G241DCU	VSOOP (8)	2.30 mm × 2.00 mm
SN74LVC2G241YZP	DSBGA (8)	1.91 mm × 0.91 mm

(1) For all available packages, see the orderable addendum at the end of the data sheet.

Logic Diagram (Positive Logic)

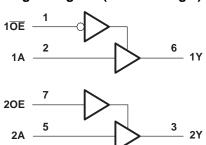




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4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

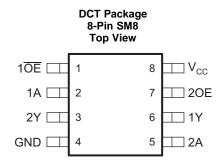
CI	hanges from Revision O (December 2015) to Revision P	Page
•	Changed Electrical Characteristics table format	
CI	hanges from Revision N (November 2013) to Revision O	Page
•	Added Applications section, Device Information table, ESD Ratings table, Thermal Information table, Typical Characteristics, Feature Description section, Device Functional Modes, Application and Implementation section, Power Supply Recommendations section, Layout section, Device and Documentation Support section, and Mechanical, Packaging, and Orderable Information section.	1
CI	hanges from Revision M (February 2007) to Revision N	Page
•	Updated document to new TI data sheet format	
•	Removed Ordering Information table.	1
•	Updated Features.	1
•	Updated operating temperature range.	4

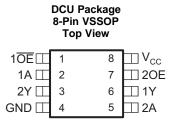
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5 Pin Configuration and Functions





YZP Package 8-Pin DSBGA Bottom View

GND	O4 5O	2A
2Y	O3 6O	1Y
1A	0270	20E
1 OE	O18O	V _{cc}

Pin Functions (1)(2)

PIN		1/0	DECEDIPTION				
NAME	NO.	1/0	DESCRIPTION				
1A	2	1	Input				
10E	1	I	Output enable (Active low)				
1Y	6	0	Output				
2A	5	1	Input				
2Y	3	0	Output				
20E	7	1	Output enable (Active high)				
GND	4	_	Ground				
V _{CC}	8	_	Power pin				

- (1) N.C. No internal connection
- (2) See for dimensions

Product Folder Links: SN74LVC2G241

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6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

			MIN	MAX	UNIT
V _{CC}	Supply voltage		-0.5	6.5	V
VI	Input voltage (2)		-0.5	6.5	V
Vo	Voltage applied to any output in the high-impedance	or power-off state (2)	-0.5	6.5	V
Vo	Voltage applied to any output in the high or low state (2)(3)		-0.5	V _{CC} + 0.5	V
I _{IK}	Input clamp current	V ₁ < 0		-50	mA
I _{OK}	Output clamp current	V _O < 0		-50	mA
Io	Continuous output current	·		±50	mA
	Continuous current through V _{CC} or GND			±100	mA
TJ	Maximum junction temperature			150	°C
T _{stg}	Storage temperature		-65	150	°C

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

6.2 ESD Ratings

			VALUE	UNIT
		Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins (1)	±2000	
V _(ESD)	Electrostatic discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101, all pins (2)	±1000	V

⁽¹⁾ JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions⁽¹⁾

			MIN	MAX	UNIT	
V	Cumply voltage	Operating	1.65	5.5	V	
V_{CC}	Supply voltage	Data retention only	1.5		V	
		V _{CC} = 1.65 V to 1.95 V	0.65 × V _{CC}			
\/	High level input voltage	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.7		V	
V _{IH}	High-level input voltage	$V_{CC} = 3 \text{ V to } 3.6 \text{ V}$	2		V	
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	$0.7 \times V_{CC}$			
		V _{CC} = 1.65 V to 1.95 V		$0.35 \times V_{CC}$		
\/	Low-level input voltage	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		0.7	V	
V_{IL}		$V_{CC} = 3 \text{ V to } 3.6 \text{ V}$		0.8	V	
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		$0.3 \times V_{CC}$		
V_{I}	Input voltage	·	0	5.5	V	
\/	Output valtage	High or low state	0	V_{CC}	V	
Vo	Output voltage	3-state	0	5.5	V	
		V _{CC} = 1.65 V		-4		
	High-level output current	V _{CC} = 2.3 V		-8		
I_{OH}		V _{CC} = 3 V		-16	mA	
		v _{CC} = 3 v		-24		
		V _{CC} = 4.5 V		-32		

All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report Implications of Slow or Floating CMOS Inputs, SCBA004.

Product Folder Links: SN74LVC2G241

⁽²⁾ The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.

⁽³⁾ The value of V_{CC} is provided in the *Recommended Operating Conditions* table.

⁽²⁾ JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



Recommended Operating Conditions⁽¹⁾ (continued)

			MIN MAX	UNIT
		V _{CC} = 1.65 V	4	
		V _{CC} = 2.3 V	8	
I _{OL}	Low-level output current	V 2 V	16	mA
		$V_{CC} = 3 V$	24	
		V _{CC} = 4.5 V	32	
	Input transition rise or fall rate	$V_{CC} = 1.8 \text{ V} \pm 0.15 \text{ V}, 2.5 \text{ V} \pm 0.2 \text{ V}$	20	
Δt/Δν		$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	10	ns/V
		$V_{CC} = 5 V \pm 0.5 V$	5	
T _A Operating free-air temperature		-40 85	°C	

6.4 Thermal Information

THERMAL METRIC ⁽¹⁾					
		DCT (SM8)	DCU (VSSOP)	YZP (DSBGA)	UNIT
		8 PINS	8 PINS	8 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	220	227	102	°C/W

For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report, SPRA953.

6.5 Electrical Characteristics

over recommended operating free-air temperature range, $T_A = -40$ °C to 125°C (unless otherwise noted)

PARAMETER		TEST CONDITIONS	V _{cc}	–40°C to 85°C			-40°C to 125°C (Recommended)			UNIT
				MIN	TYP	MAX	MIN	TYP	MAX	
		$I_{OH} = -100 \mu A$	1.65 V to 5.5 V	V _{CC} - 0.1			$V_{CC} - 0.1$			
		$I_{OH} = -4 \text{ mA}$	1.65 V	1.2			1.2			
.,		$I_{OH} = -8 \text{ mA}$	2.3 V	1.9			1.9			V
V _{OH}		$I_{OH} = -16 \text{ mA}$	3 V	2.4			2.4			V
		$I_{OH} = -24 \text{ mA}$	3 V	2.3			2.3			
		I _{OH} = -32 mA	4.5 V	3.8			3.8			
		I _{OL} = 100 μA	1.65 V to 5.5 V			0.1			0.1	
		I _{OL} = 4 mA	1.65 V			0.45			0.45	
		I _{OL} = 8 mA	2.3 V			0.3			0.3	V
V _{OL}		I _{OL} = 16 mA	3 V			0.4			0.4	V
		I _{OL} = 24 mA	3 V			0.55			0.55	
		I _{OL} = 32 mA	4.5 V			0.55			0.75	
I	A or OE inputs	V _I = 5.5 V or GND	0 to 5.5 V			±5			±5	μΑ
I _{off}		V_I or $V_O = 5.5 \text{ V}$	0			±10			±10	μΑ
loz		V _O = 0 to 5.5 V	3.6 V			10			10	μΑ
I _{CC}		$V_I = 5.5 \text{ V or GND}, \qquad I_O = 0$	1.65 V to 5.5 V			10			10	μΑ
ΔI_{CC}		One input at $V_{CC} - 0.6 \text{ V}$, Other inputs at V_{CC} or GND	3 V to 5.5 V			500			500	μΑ
	Data Inputs	V V or CND	221/		3.5					~F
Ci	Control Inputs	$V_I = V_{CC}$ or GND	3.3 V		4					pF
Co		V _O = V _{CC} or GND	3.3 V		6.5					pF

Product Folder Links: SN74LVC2G241



6.6 Switching Characteristics

over recommended operating free-air temperature range (unless otherwise noted) (see Figure 2)

		1 0	`			, ,	-	,			
						-40°C 1	o 85°C				
PARAMETER	FROM (INPUT)			V _{CC} = 1.8 V		V _{CC} = 3.3 V ± 0.3 V		V _{CC} = 5 V ± 0.5 V		UNIT	
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t _{pd}	Α	Υ	3.3	9.1	1.5	5.5	1.4	4.3	1.0	4.0	ns
t _{en}	ŌĒ	Υ	4.0	9.9	1.3	6.6	1.2	4.7	1.1	5.0	ns
t _{dis}	ŌĒ	Υ	1.5	11.6	1.0	5.7	1.4	4.6	0.5	4.2	ns

			-40°C to 125°C (Recommended)									
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC} = 1 ± 0.15		V _{CC} = 2 ± 0.2		V _{CC} = 3 ± 0.3		V _{CC} = ± 0.5	5 V V	UNIT	
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX		
t _{pd}	Α	Y	3.3	10.1	1.5	5.6	1.4	5.3	1.0	4.2	ns	
t _{en}	ŌĒ	Υ	4.0	10.9	1.3	6.6	1.2	5.7	1.2	4.3	ns	
t _{dis}	ŌE	Y	1.5	12.6	1.0	6.6	1.4	5.6	1.0	3.9	ns	

6.7 Operating Characteristics

 $T_{\Delta} = 25^{\circ}C$

	PARAME	TER	TEST CONDITIONS	V _{cc}	TYP	UNIT	
Power dissipation				V _{CC} = 1.8 V	19		
	Outputs anabled		V _{CC} = 2.5 V	19	pF		
	Outputs enabled		$V_{CC} = 3.3 \text{ V}$	20	ρı		
		f = 10 MHz	$V_{CC} = 5 V$	22			
C _{pd}	capacitance per buffer/driver		T = TO IVITIZ	$V_{CC} = 1.8 \text{ V}$	2		
		Outputs disabled		$V_{CC} = 2.5 \text{ V}$	2	, r	
		Outputs disabled		$V_{CC} = 3.3 \text{ V}$	2	pF	
				$V_{CC} = 5 V$	3		

6.8 Typical Characteristic

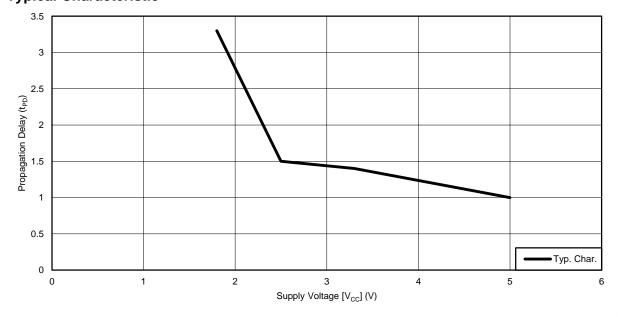


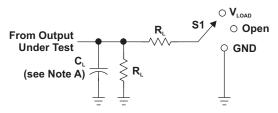
Figure 1. tpd vs Vcc Over Full Temperature Range

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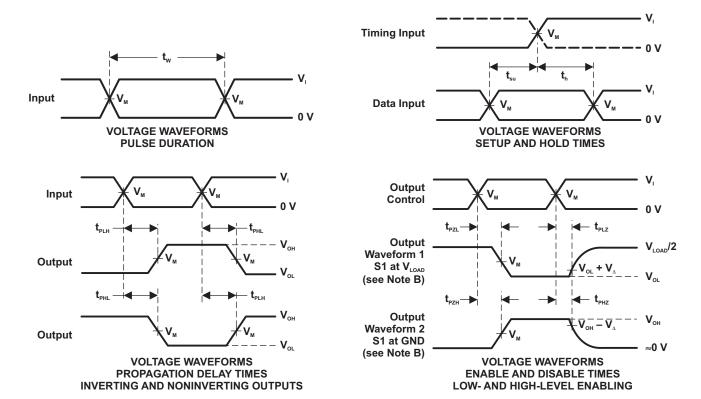
7 Parameter Measurement Information



TEST	S1
t _{PLH} /t _{PHL}	Open
t _{PLZ} /t _{PZL}	V _{LOAD}
t _{PHZ} /t _{PZH}	GND

LOAD CIRCUIT

.,	INI	PUTS		.,			.,
V _{cc}	V _{cc} V _i		V _M	V _{LOAD}	C _L	R _∟	V _Δ
1.8 V ± 0.15 V	V _{cc}	≤2 ns	V _{cc} /2	2 × V _{cc}	30 pF	1 k Ω	0.15 V
2.5 V ± 0.2 V	V_{cc}	≤2 ns	V _{cc} /2	2 × V _{cc}	30 pF	500 Ω	0.15 V
3.3 V ± 0.3 V	3 V	≤2.5 ns	1.5 V	6 V	50 pF	500 Ω	0.3 V
5 V ± 0.5 V	V_{cc}	≤2.5 ns	V _{cc} /2	2 × V _{cc}	50 pF	500 Ω	0.3 V



NOTES: A. C, includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z_{o} = 50 Ω .
- D. The outputs are measured one at a time, with one transition per measurement.
- E. t_{PLZ} and \dot{t}_{PHZ} are the same as t_{dis} .
- F. $t_{\mbox{\tiny PZL}}$ and $t_{\mbox{\tiny PZH}}$ are the same as $t_{\mbox{\tiny en}}.$
- G. t_{PlH} and t_{PHl} are the same as t_{pd} .
- H. All parameters and waveforms are not applicable to all devices.

Figure 2. Load Circuit and Voltage Waveforms

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8 Detailed Description

8.1 Overview

The SN74LVC2G241 device is designed specifically to improve both the performance and density of 3-state memory-address drivers, clock drivers, and bus-oriented receivers and transmitters. The SN74LVC2G241 device is organized as two 1-bit line drivers with separate output-enable (1OE, 2OE) inputs. When 1OE is low and 2OE is high, the device passes data from the A inputs to the Y outputs. When 1OE is high and 2OE is low, the outputs are in the high-impedance state.

The SN74LVC2G241 is also an effective redriver, with a maximum output current drive of 32 mA.

8.2 Functional Block Diagram

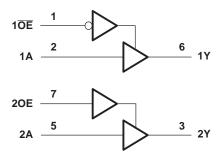


Figure 3. Logic Diagram (Positive Logic)

8.3 Feature Description

To ensure the high-impedance state during power up or power down, \overline{OE} should be tied to V_{CC} through a pullup resistor, and OE should be tied to GND through a pulldown resistor; the minimum value of the resistor is determined by the current-sinking or the current-sourcing capability of the driver.

This device is fully specified for partial-power-down applications using I_{off}. The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

8.4 Device Functional Modes

Table 1 and Table 2 list the functional modes of the SN74LVC2G241.

Table 1. Gate 1 Functional Table

INI	PUTS	OUTPUT
1 OE	1A	1Y
L	Н	Н
L	L	L
Н	X	Z

Table 2. Gate 2 Functional Table

INI	PUTS	OUTPUT
20E	2A	2Y
Н	Н	Н
Н	L	L
L	X	Z

Product Folder Links: SN74LVC2G241



9 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

Typical Application shows a simple application where a physical push button is connected to the SN74LVC2G241. The push button is in a physical location far enough away from the processor that the input signal is weak and needs to be redriven. The SN74LVC2G241 acts as a redriver, providing a strong input signal to the processor with as little as 1 ns of propagation delay.

9.2 Typical Application

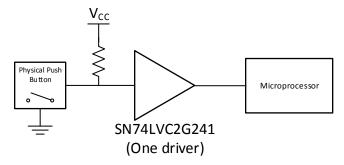


Figure 4. SN74LVC2G241 Application

9.2.1 Design Requirements

This device uses CMOS technology and has balanced output drive. Take care to avoid bus contention because it can drive currents that would exceed maximum limits. The high drive also creates fast edges into light loads, so routing and load conditions must be considered to prevent ringing.

9.2.2 Detailed Design Procedure

- Recommended Input Conditions
 - Rise time and fall time specs. See (Δt/ΔV) in Recommended Operating Conditions.
 - Specified high and low levels. See (V_{IH} and V_{IL}) in Recommended Operating Conditions.
 - Inputs are overvoltage tolerant allowing them to go as high as (V_I max) in Recommended Operating
 Conditions at any valid V_{CC}.

2. Recommend Output Conditions

Load currents must not exceed (I_O max) per output and must not exceed (Continuous current through V_{CC} or GND) total current for the part. These limits are located in Absolute Maximum Ratings.

Product Folder Links: SN74LVC2G241

Outputs must not be pulled above V_{CC} during normal operation or 5.5 V in high-z state.

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Typical Application (continued)

9.2.3 Application Curve

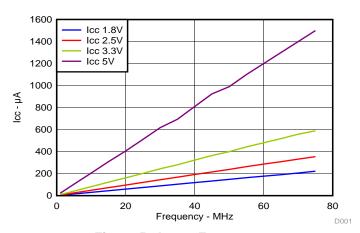


Figure 5. I_{CC} vs Frequency

10 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in *Recommended Operating Conditions*.

Each V_{CC} pin should have a good bypass capacitor to prevent power disturbance. For devices with a single supply, a 0.1- μ F capacitor is recommended and if there are multiple V_{CC} pins then a 0.01- μ F or 0.022- μ F capacitor is recommended for each power pin. It is ok to parallel multiple bypass capacitors to reject different frequencies of noise. 0.1- μ F and 1- μ F capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power pin as possible for best results.

11 Layout

11.1 Layout Guidelines

When using multiple bit logic devices inputs must not ever float. In many cases, functions or parts of functions of digital logic devices are unused; for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used. Such input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. Specified below are the rules that must be observed under all circumstances. All unused inputs of digital logic devices must be connected to a high or low bias to prevent them from floating. The logic level that should be applied to any particular unused input depends on the function of the device. Generally they will be tied to GND or V_{CC} , whichever make more sense or is more convenient.

11.2 Layout Example



Figure 6. Layout Diagram

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12 Device and Documentation Support

12.1 Documentation Support

12.1.1 Related Documentation

For related documentation, see the following:

Implications of Slow or Floating CMOS Inputs, SCBA004

12.2 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™ Online Community TI's Engineer-to-Engineer (E2E) Community. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

12.3 Trademarks

NanoFree, E2E are trademarks of Texas Instruments. All other trademarks are the property of their respective owners.

12.4 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

12.5 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical packaging and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser based versions of this data sheet, refer to the left hand navigation.

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PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package	Pins	Package	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
74LVC2G241DCTRE4	ACTIVE	SM8	DCT	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	C41 Z	Samples
74LVC2G241DCTRG4	ACTIVE	SM8	DCT	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	C41 Z	Samples
74LVC2G241DCUTG4	ACTIVE	VSSOP	DCU	8	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	C41R	Samples
SN74LVC2G241DCTR	ACTIVE	SM8	DCT	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	C41 Z	Samples
SN74LVC2G241DCUR	ACTIVE	VSSOP	DCU	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU CU SN	Level-1-260C-UNLIM	-40 to 125	(C41Q, C41R)	Samples
SN74LVC2G241DCUT	ACTIVE	VSSOP	DCU	8	250	Green (RoHS & no Sb/Br)	CU NIPDAU CU SN	Level-1-260C-UNLIM	-40 to 125	(C41Q, C41R)	Samples
SN74LVC2G241YZPR	ACTIVE	DSBGA	YZP	8	3000	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM	-40 to 125	(C2, C27)	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.



PACKAGE OPTION ADDENDUM

3-Dec-2018

(6) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
74LVC2G241DCUTG4	VSSOP	DCU	8	250	180.0	8.4	2.25	3.35	1.05	4.0	8.0	Q3
SN74LVC2G241DCTR	SM8	DCT	8	3000	180.0	13.0	3.35	4.5	1.55	4.0	12.0	Q3
SN74LVC2G241DCUR	VSSOP	DCU	8	3000	178.0	9.5	2.25	3.35	1.05	4.0	8.0	Q3
SN74LVC2G241DCUR	VSSOP	DCU	8	3000	180.0	8.4	2.25	3.35	1.05	4.0	8.0	Q3
SN74LVC2G241DCUT	VSSOP	DCU	8	250	178.0	9.5	2.25	3.35	1.05	4.0	8.0	Q3
SN74LVC2G241YZPR	DSBGA	YZP	8	3000	180.0	8.4	1.02	2.02	0.63	4.0	8.0	Q1

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*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
74LVC2G241DCUTG4	VSSOP	DCU	8	250	202.0	201.0	28.0
SN74LVC2G241DCTR	SM8	DCT	8	3000	182.0	182.0	20.0
SN74LVC2G241DCUR	VSSOP	DCU	8	3000	202.0	201.0	28.0
SN74LVC2G241DCUR	VSSOP	DCU	8	3000	202.0	201.0	28.0
SN74LVC2G241DCUT	VSSOP	DCU	8	250	202.0	201.0	28.0
SN74LVC2G241YZPR	DSBGA	YZP	8	3000	210.0	185.0	35.0

DCU (R-PDSO-G8)

PLASTIC SMALL-OUTLINE PACKAGE (DIE DOWN)



NOTES:

- A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
 - D. Falls within JEDEC MO-187 variation CA.



DCU (S-PDSO-G8)

PLASTIC SMALL OUTLINE PACKAGE (DIE DOWN)



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



DCT (R-PDSO-G8)

PLASTIC SMALL-OUTLINE PACKAGE



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion
- D. Falls within JEDEC MO-187 variation DA.

DCT (R-PDSO-G8)

PLASTIC SMALL OUTLINE



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.





DIE SIZE BALL GRID ARRAY



NOTES:

- All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.



DIE SIZE BALL GRID ARRAY



NOTES: (continued)

3. Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. For more information, see Texas Instruments literature number SNVA009 (www.ti.com/lit/snva009).



DIE SIZE BALL GRID ARRAY



NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.



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